2SB1463J

Silicon PNP epitaxial planar type

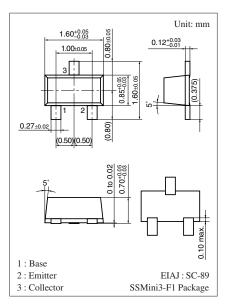
For high breakdown voltage low-noise amplification Complementary to 2SC2440J

Features

- \bullet High collector-emitter voltage (Base open) $V_{\mbox{CEO}}$
- Low noise voltage NV
- SS-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing.

Absolute Maximum Ratings $T_a = 25^{\circ}C$

| 0 " | | | | | | |
|------------------|--|--|--|--|--|--|
| Symbol | Rating | Unit | | | | |
| V _{CBO} | -150 | V | | | | |
| V _{CEO} | -150 | V | | | | |
| V _{EBO} | -5 | V | | | | |
| I _C | -50 | mA | | | | |
| I _{CP} | -100 | mA | | | | |
| P _C | 125 | mW | | | | |
| Tj | 125 | °C | | | | |
| T _{stg} | -55 to +125 | °C | | | | |
| | V_{CBO} V_{CEO} V_{EBO} I_C I_{CP} P_C T_j | $\begin{array}{c c c c c c c c c c c c c c c c c c c $ | | | | |



Marking Symbol: I

Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

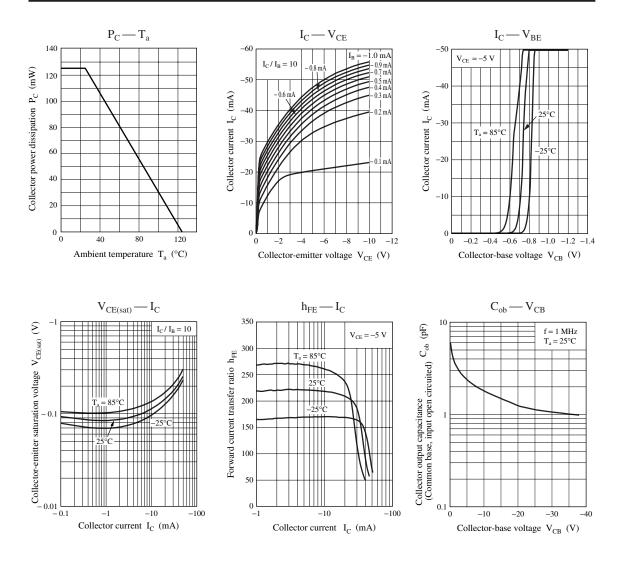
| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|---|----------------------|---|------|-----|-----|------|
| Collector-emitter voltage (Base open) | V _{CEO} | $I_{C} = -100 \ \mu A, \ I_{B} = 0$ | -150 | | | V |
| Emitter-base voltage (Collector open) | V _{EBO} | $I_{\rm E} = -10 \ \mu A, \ I_{\rm C} = 0$ | -5 | | | V |
| Collector-base cutoff current (Emitter open) | I _{CBO} | $V_{CB} = -100 \text{ V}, I_E = 0$ | | | -1 | μΑ |
| Forward current transfer ratio * | h _{FE} | $V_{CE} = -5 \text{ V}, I_C = -10 \text{ mA}$ | 130 | | 330 | |
| Collector-emitter saturation voltage | V _{CE(sat)} | $I_{\rm C} = -30$ mA, $I_{\rm B} = -3$ mA | | | -1 | V |
| Transition frequency | f _T | $V_{CB} = -10 \text{ V}, I_E = 10 \text{ mA}, f = 200 \text{ MHz}$ | | 200 | | MHz |
| Collector output capacitance (Common base, input open circuited) | C _{ob} | $V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ | | 4 | | pF |
| Noise voltage | NV | $V_{CE} = -10 \text{ V}, I_C = -1 \text{ mA}, G_V = 80 \text{ dB}$ $R_g = 100 \text{ k}\Omega, \text{ Function} = \text{FLAT}$ | | 150 | | mV |

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

| Rank | R | S |
|-----------------|------------|------------|
| h _{FE} | 130 to 220 | 185 to 330 |

Panasonic



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